

NX138AKSF Datasheet

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DiGi Electronics Part Number NX138AKSF-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number NX138AKSF

Description MOSFET 2N-CH 60V 0.17A 6TSSOP

Detailed Description Mosfet Array 60V 170mA (Ta) 1.33W Surface Mount

6-TSSOP



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
NX138AKSF	Nexperia USA Inc.
Series:	Product Status:
	Active
Technology:	Configuration:
MOSFET (Metal Oxide)	2 N-Channel (Dual)
FET Feature:	Drain to Source Voltage (Vdss):
	60V
Current - Continuous Drain (Id) @ 25°C:	Rds On (Max) @ ld, Vgs:
170mA (Ta)	4.50hm @ 170mA, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
1.5V @ 250µA	1.4nC @ 10V
Input Capacitance (Ciss) (Max) @ Vds:	Power - Max:
20pF @ 30V	1.33W
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Package / Case:	Supplier Device Package:
6-TSSOP, SC-88, SOT-363	6-TSSOP
Base Product Number:	
NX138	

Environmental & Export classification

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	

Product data sheet

1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- · Very fast switching
- · Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection

3. Applications

- Relay driver
- · High-speed line driver
- · Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	•				'	-	
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	170	mA
Static charac	teristics (per transistor)		'				
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 170 \text{ mA}; T_j = 25 \text{ °C}$		-	3	4.5	Ω

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².



60 V, dual N-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		D1 D2
2	G1	gate TR1	654	
3	D2	drain TR2		G1 A A B G2
4	S2	source TR2	0	
5	G2	gate TR2	1 2 3	
6	D1	drain TR1	TSSOP6 (SOT363)	S1 S2 017aaa256

6. Ordering information

Table 3. Ordering information

Type number	Package	Package					
	Name	Description	Version				
NX138AKS		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363				

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
NX138AKS	F8%

[1] % = placeholder for manufacturing site code

60 V, dual N-channel Trench MOSFET

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transiste	or				'	
V _{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	170	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	110	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	680	mA
P _{tot} tot	total power dissipation	T _{amb} = 25 °C	[2]	-	265	mW
			[1]	-	325	mW
		T _{sp} = 25 °C		-	1.33	W
Per device	•					
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	n diode					
Is	source current	T _{amb} = 25 °C	[1]	-	170	mA

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

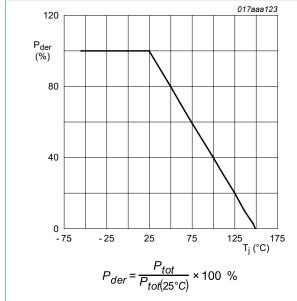


Fig. 1. MOSFET transistor: Normalized total power dissipation as a function of junction temperature

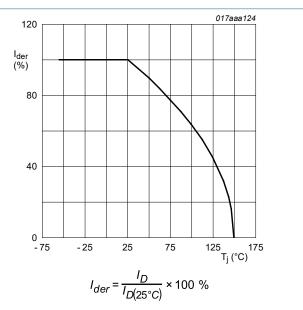


Fig. 2. MOSFET transistor: Normalized continuous drain current as a function of junction temperature

60 V, dual N-channel Trench MOSFET

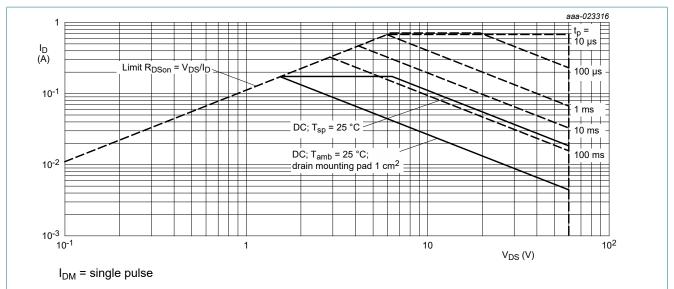


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

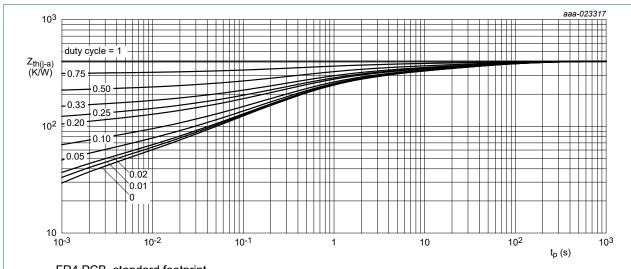
60 V, dual N-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

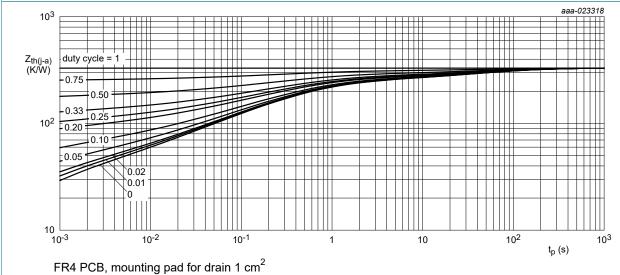
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
ui(j-a)		o ambient	[1]	-	500	560	K/W
	junction to ambient		[2]	-	450	480	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	100	115	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm².



FR4 PCB, standard footprint

Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 4.



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

60 V, dual N-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics (per transistor)					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.8	1.1	1.5	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μΑ
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-2	μΑ
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.5	μΑ
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-0.5	μΑ
		V _{GS} = 5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 170 mA; T _j = 25 °C	-	3	4.5	Ω
	resistance	V _{GS} = 10 V; I _D = 170 mA; T _j = 150 °C	-	6	9	Ω
		$V_{GS} = 5 \text{ V}; I_D = 150 \text{ mA}; T_j = 25 ^{\circ}\text{C}$	-	3.7	5.2	Ω
		$V_{GS} = 4 \text{ V}; I_D = 130 \text{ mA}; T_j = 25 ^{\circ}\text{C}$	-	4	6.3	Ω
		V_{GS} = 2.5 V; I_{D} = 100 mA; T_{j} = 25 °C	-	5	10	Ω
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 170 \text{ mA}; T_j = 25 \text{ °C}$	-	3.5	-	S
Dynamic ch	naracteristics (per transist	or)	,			
Q _{G(tot)}	total gate charge	V _{DS} = 30 V; I _D = 170 mA; V _{GS} = 10 V;	-	0.9	1.4	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.1	-	nC
Q_{GD}	gate-drain charge		-	0.2	-	nC
C _{iss}	input capacitance	V _{DS} = 30 V; f = 1 MHz; V _{GS} = 0 V;	-	15	20	pF
C _{oss}	output capacitance	T _j = 25 °C	-	2.3	-	pF
C _{rss}	reverse transfer capacitance		-	1.5	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 30 V; I _D = 170 mA; V _{GS} = 10 V;	-	8	12	ns
t _r	rise time	$R_{G(ext)} = 75 \Omega; T_j = 25 °C$	-	10	-	ns
t _{d(off)}	turn-off delay time		-	8	20	ns
t _f	fall time	7	-	5	-	ns
Source-dra	in diode (per transistor)	'	1			
V _{SD}	source-drain voltage	I _S = 170 mA; V _{GS} = 0 V; T _j = 25 °C	-	0.8	1.2	V

60 V, dual N-channel Trench MOSFET

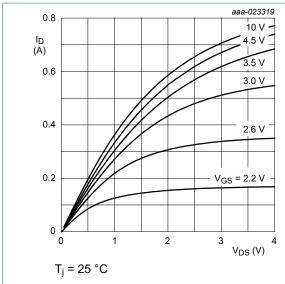


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

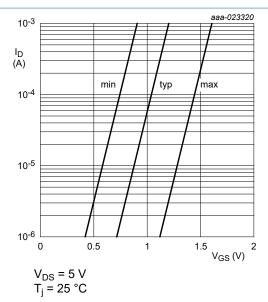


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

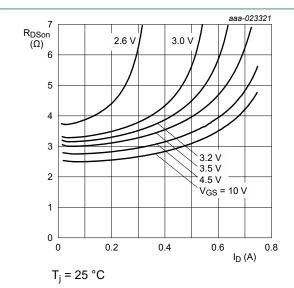


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

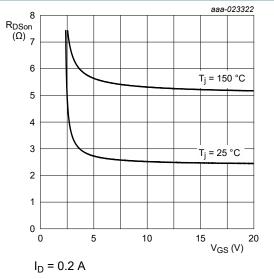


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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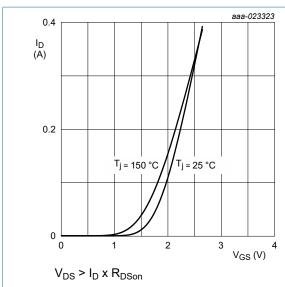


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

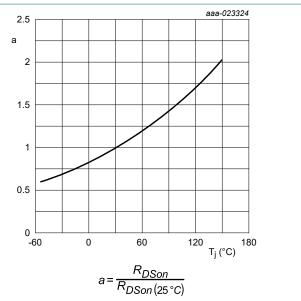


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

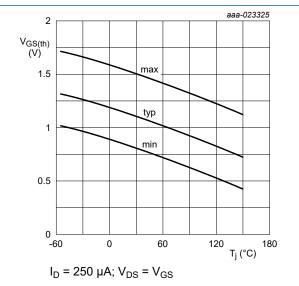
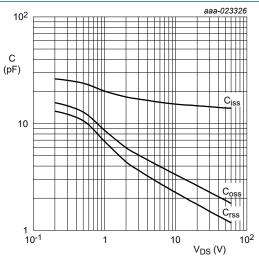


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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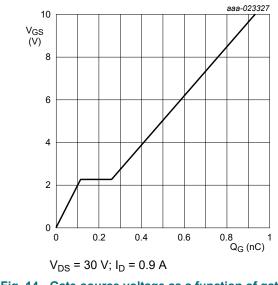


Fig. 14. Gate-source voltage as a function of gate charge; typical values

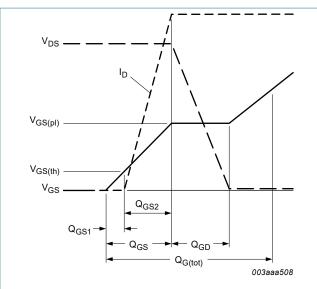


Fig. 15. Gate charge waveform definitions

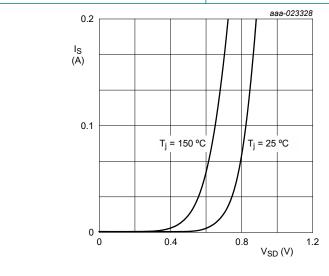
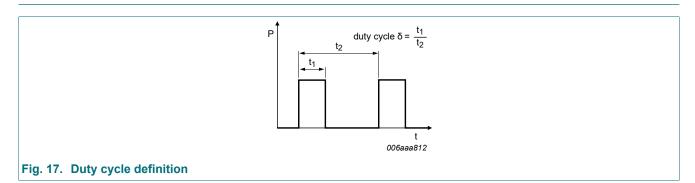


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



60 V, dual N-channel Trench MOSFET

12. Package outline

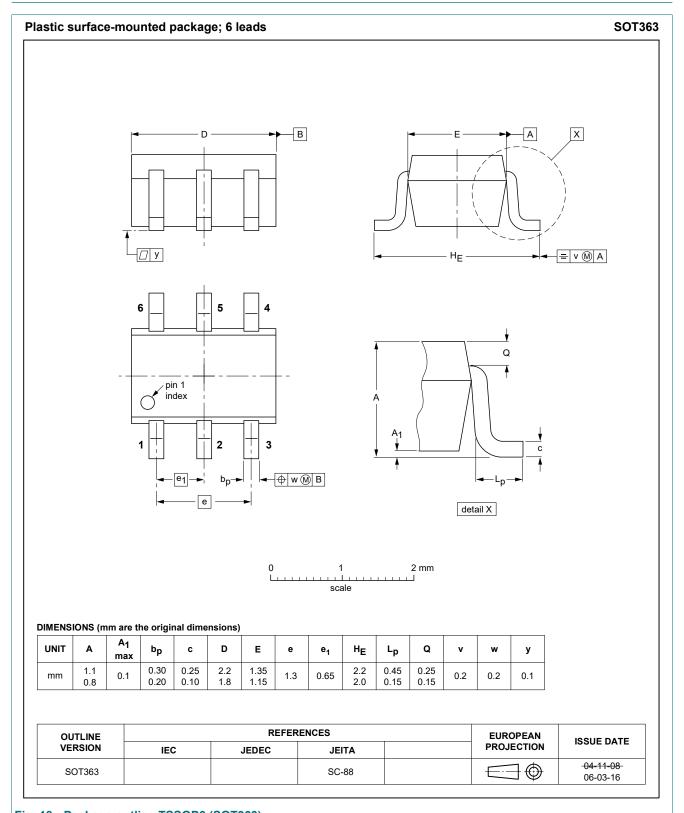
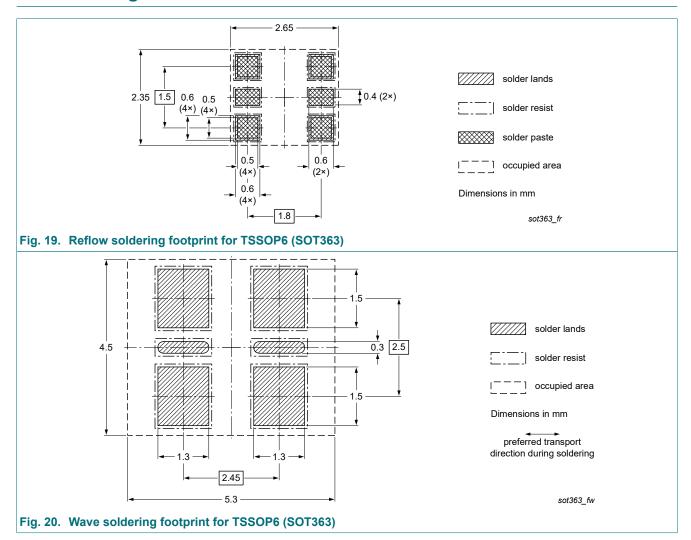


Fig. 18. Package outline TSSOP6 (SOT363)

60 V, dual N-channel Trench MOSFET

13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
NX138AKS v.2	20240202	Product data sheet	-	NX138AKS v.1			
Modifications:	Chapter "Chair	Chapter "Characteristics": typo correction for one R _{DSon} condition					
NX138AKS v.1	20160615	Product data sheet	-	-			

60 V, dual N-channel Trench MOSFET

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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60 V, dual N-channel Trench MOSFET

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